

# 2SC6120

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON NPN EPITAXIAL TYPE

## DESCRIPTION

2SC6120 is a silicon NPN epitaxial type transistor designed with high collector current, low  $V_{CE(sat)}$ .

## FEATURE

- High collector current

$$I_{C(MAX)} = 600\text{mA}$$

- Low collector to emitter saturation voltage

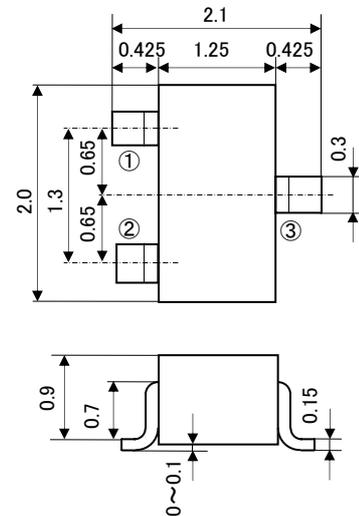
$$V_{CE(sat)} < 0.3V_{max}(I_C=150\text{mA}, I_B=15\text{mA})$$

## APPLICATION

For switching application, small type motor drive application.

## OUTLINE DRAWING

Unit: mm



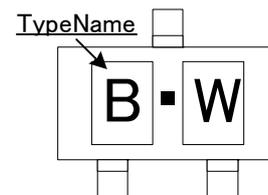
### TERMINAL CONNECTOR

- ①: BASE EIAJ: SC-70
- ②: EMITTER JEDEC: -
- ③: COLLECTOR

## MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

記号	項目	定格値	単位
$V_{CEO}$	Collector to Emitter voltage	40	V
$V_{CBO}$	Collector to Base voltage	75	V
$V_{EBO}$	Emitter to Base voltage	6	V
$I_C$	Collector current	600	mA
$P_C$	Collector dissipation	150	mW
$T_j$	Junction temperature	+150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55~+150	$^\circ\text{C}$

## MARKING

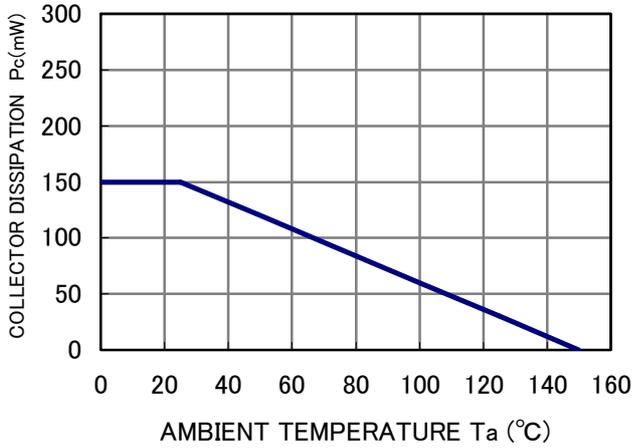


## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ )

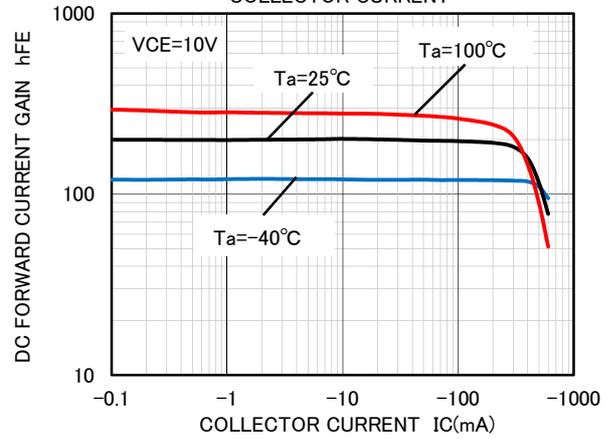
Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E break down voltage	$I_C=1\text{mA}, I_B=0$	40	—	—	V
$V_{(BR)CBO}$	C to B break down voltage	$I_C=10\mu\text{A}, I_E=0$	75	—	—	V
$V_{(BR)EBO}$	E to B break down voltage	$I_E=10\mu\text{A}, I_C=0$	6	—	—	V
$I_{CBO}$	Collector cut off current	$V_{CB}=60\text{V}, I_E=0$	—	—	100	nA
$I_{EBO}$	Emitter cut off current	$V_{EB}=3\text{V}, I_C=0$	—	—	100	nA
$h_{FE}$	DC forward current gain	$I_C=150\text{mA}, V_{CE}=10\text{V}$	100	—	300	—
$V_{CE(sat)}$	C to E saturation voltage	$I_C=150\text{mA}, I_B=15\text{mA}$	—	—	0.3	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C=150\text{mA}, I_B=15\text{mA}$	0.6	—	1.2	V
$f_T$	Gain band width product	$I_E=-20\text{mA}, V_{CE}=20\text{V}, f=100\text{MHz}$	—	250	—	MHz
$C_{ob}$	Collector output capacitance	$V_{CB}=10\text{V}, f=1\text{MHz}$	—	—	8	pF

## TYPICAL CHARACTERISTICS

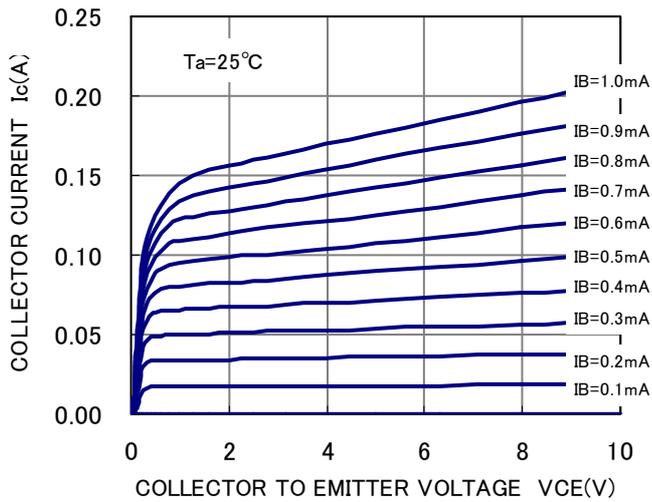
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



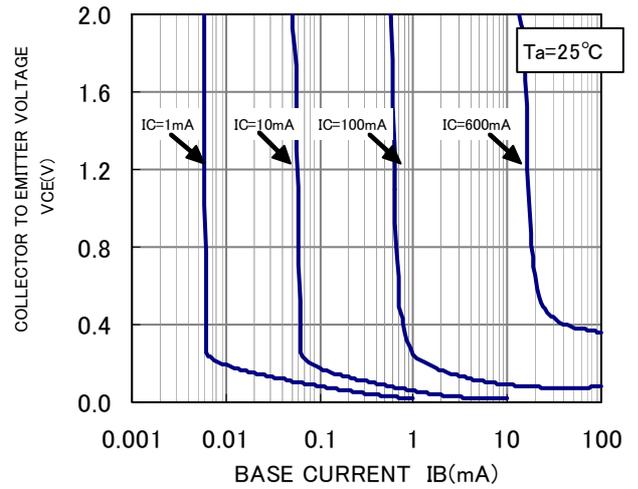
DC FORWARD CURRENT GAIN VS. COLLECTOR CURRENT



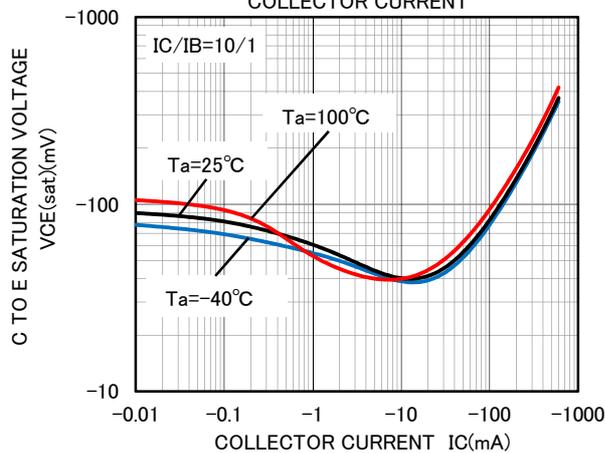
COMMON EMITTER OUTPUT



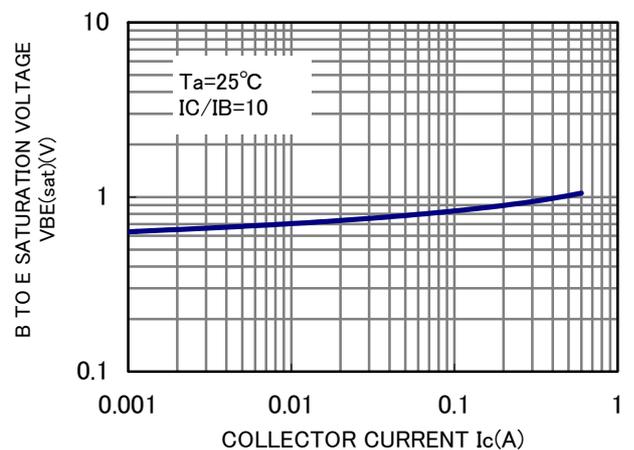
COLLECTOR TO EMITTER VOLTAGE VS. BASE CURRENT



C TO E SATURATION VOLTAGE VS. COLLECTOR CURRENT



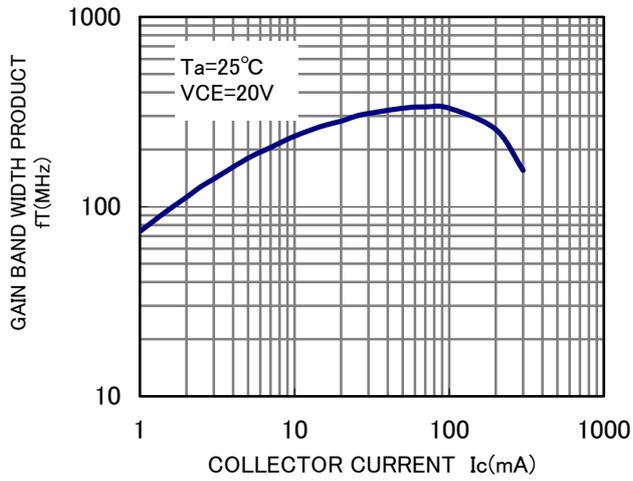
B TO E SATURATION VOLTAGE VS. COLLECTOR CURRENT



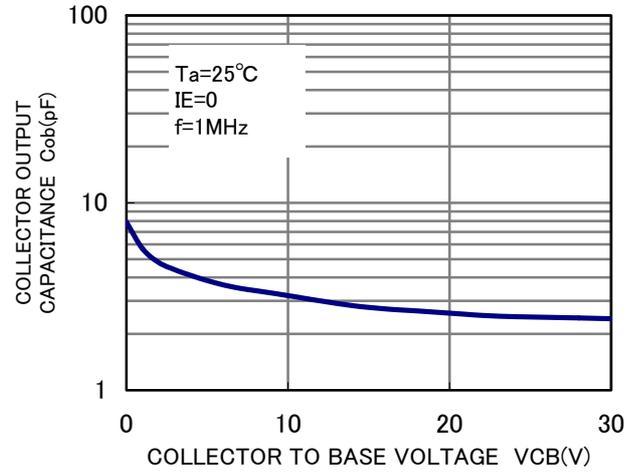
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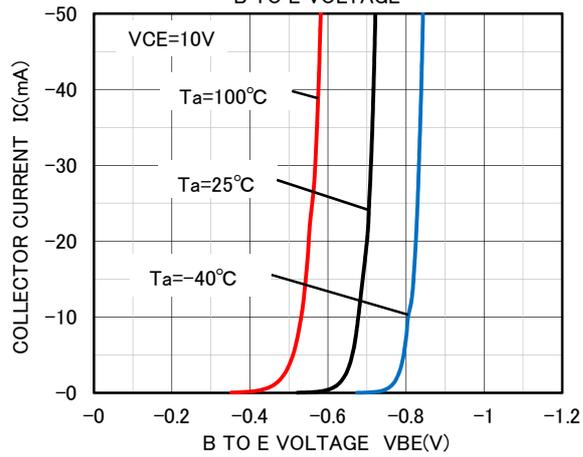
GAIN BAND WIDTH PRODUCT VS.  
COLLECTOR CURRENT



COLLECTOR OUTPUT CAPACITANCE VS.  
COLLECTOR TO BASE VOLTAGE



COLLECTOR CURRENT VS.  
B TO E VOLTAGE





6-41 Tsukuba, Isahaya, Nagasaki, 854-0065 Japan

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